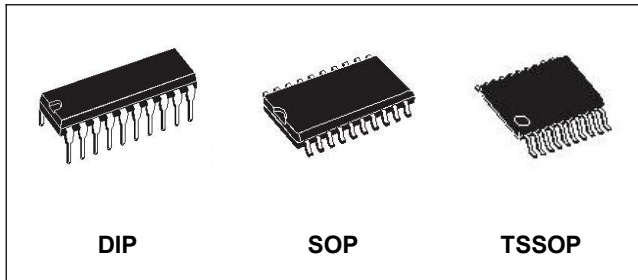


OCTAL D-TYPE LATCH WITH 3 STATE OUTPUT NON INVERTING

Datasheet- production data



Description

The RD74HC373 is a high speed CMOS OCTAL LATCH WITH 3-STATE OUTPUTS fabricated with sub-micron silicon gate CMOS technology.

This 8-BIT D-Type latches is controlled by a latch enable input (LE) and output enable input (\overline{OE}).

While the LE input is held at a high level, the Q outputs will follow the data input. When the LE is taken low, the Q outputs will be latched at the logic level of D input data.

While the \overline{OE} input is at low level, the eight outputs will be in a normal logic state (high or low logic level) and when \overline{OE} is in high level the outputs will be in a high impedance state.

The 3-State output configuration and the wide choice of outline make bus organized system simple.

All inputs are equipped with protection circuits against static discharge and transient excess voltage.

Features

- HIGH SPEED:
 $t_{PD} = 12\text{ns}$ (TYP.) at $V_{CC} = 6\text{V}$
- LOW POWER DISSIPATION:
 $I_{CC} = 4\mu\text{A}$ (MAX.) at $T_A = 25^\circ\text{C}$
- HIGH NOISE IMMUNITY:
 $V_{NIH} = V_{NIL} = 28\% V_{CC}(\text{MIN.})$
- SYMMETRICAL OUTPUT IMPEDANCE:
 $|I_{OH}| = I_{OL} = 6\text{mA}$ (MIN.)
- BALANCED PROPAGATION DELAYS:
 $t_{PLH} \cong t_{PHL}$
- WIDE OPERATING VOLTAGE RANGE:
 $V_{CC}(\text{OPR.}) = 2\text{V to } 6\text{V}$

Table 1. Device summary

PART NUMBER	PACKAGE
RD74HC373BDI	DIP20
RD74HC373BSO	SOP20
RD74HC373BTS	TSSOP20

1 Pin information

Figure 1. Pin connection and IEC logic symbols

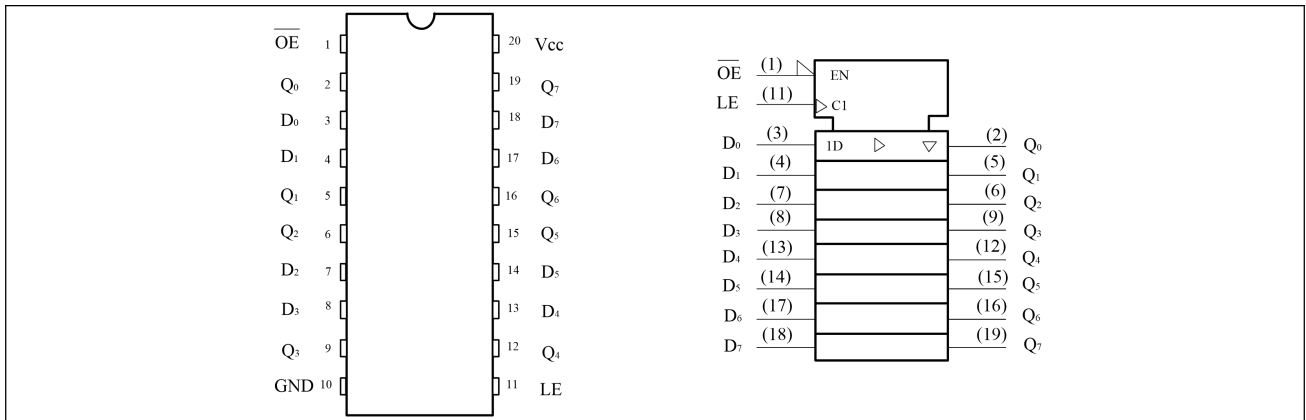


Table 2. Pin description

Pin No	Symbol	Name and function
1	\overline{OE}	3 State Output Enable Input (Active LOW)
2, 5, 6, 9, 12, 15, 16, 19	Q0 to Q7	3 State Outputs
3, 4, 7, 8, 13, 14, 17, 18	D0 to D7	Data Inputs
11	LE	Latch Enable Input
10	GND	Ground (0V)
20	V _{CC}	Positive Supply Voltage

2 Functional description

Table 3. Truth table

INPUTS			OUTPUTS
\overline{OE}	LE	D	Q
H	X	X	Z
L	L	X	NO CHANGE ^(*)
L	H	L	L
L	H	H	H

X = Don't care

Z = High impedance

(*): Q Outputs are latched at the time when the LE input is taken low logic level.

Figure 2. Input and output equivalent circuit

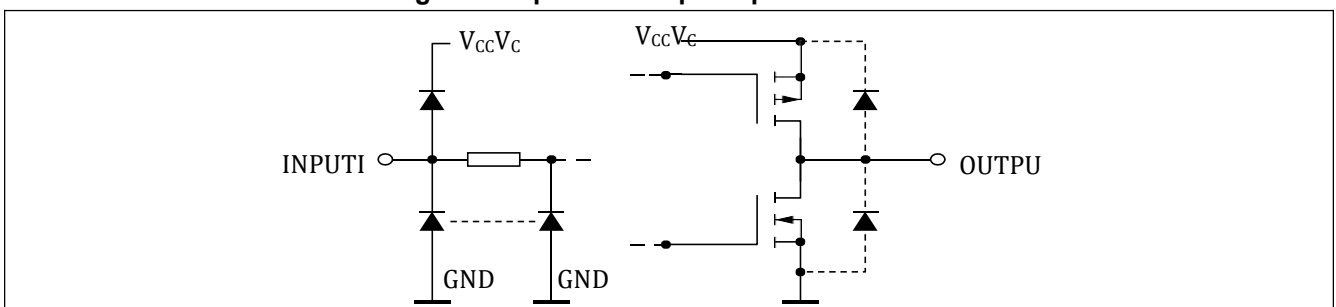
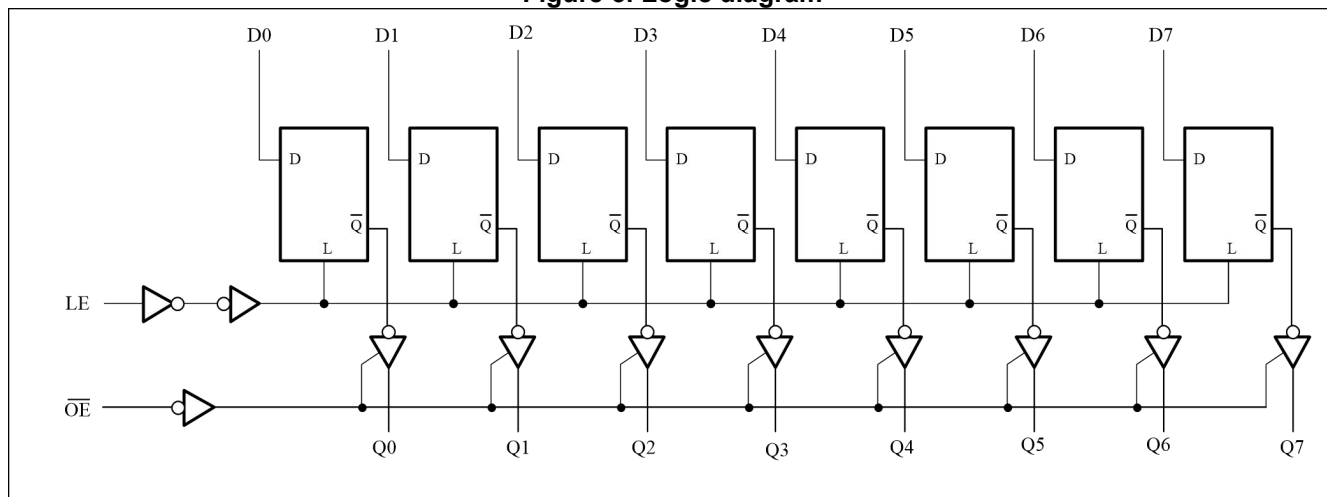


Figure 3. Logic diagram



3 Electrical characteristics

Table 4. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{CC}	Supply Voltage	-0.5 to + 7.0	V
V_I	DC Input Voltage	-0.5 to $V_{CC} + 0.5$	V
V_O	DC Output Voltage	-0.5 to $V_{CC} + 0.5$	V
I_{IK}	DC Input Diode Current	± 20	mA
I_{OK}	DC Output Diode Current	± 20	mA
I_O	DC Output Current	± 35	mA
I_{CC} or I_{GND}	DC V_{CC} or Ground Current	± 70	mA
P_D	Power Dissipation	500 (*)	mW
T_{stg}	Storage Temperature	-65 to + 150	$^{\circ}C$
T_L	Lead Temperature (10 sec)	300	$^{\circ}C$

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied

(*) 500mW at 65 $^{\circ}C$; derate to 300mW by 10mW/ $^{\circ}C$ from 65 $^{\circ}C$ to 85 $^{\circ}C$

Table 5. Recommended operating conditions

Symbol	Parameter	Value	Unit	
V_{CC}	Supply Voltage	2 to 6	V	
V_I	Input Voltage	0 to V_{CC}	V	
V_O	Output Voltage	0 to V_{CC}	V	
T_{op}	Operating Temperature	-40 to +85	$^{\circ}C$	
t_r, t_f	Input Rise and Fall Time	$V_{CC} = 2.0V$	0 to 1000	ns
		$V_{CC} = 4.5V$	0 to 500	ns
		$V_{CC} = 6.0V$	0 to 400	ns

Table 6. DC specifications

Symbol	Parameter	Test Condition		Value					Unit
		V _{CC} (V)		T _A = 25 °C			-40 to 85°C		
				Min	Typ	Max	Min	Max	
V _{IH}	High Level Input Voltage	2.0		1.5			1.5		V
		4.5		3.15			3.15		
		6.0		4.2			4.2		
V _{IL}	Low Level Input Voltage	2.0				0.5		0.5	V
		4.5				1.35		1.35	
		6.0				1.8		1.8	
V _{OH}	High Level Output Voltage	2.0	I _O =-20μA	1.9	2.0		1.9		V
		4.5	I _O =-20μA	4.4	4.5		4.4		
		6.0	I _O =-20μA	5.9	6.0		5.9		
		4.5	I _O =-6.0 mA	4.18	4.31		4.13		
		6.0	I _O =-7.8 mA	5.68	5.8		5.63		
V _{OL}	Low Level Output Voltage	2.0	I _O =20 μA		0.0	0.1		0.1	V
		4.5	I _O =20 μA		0.0	0.1		0.1	
		6.0	I _O =20 μA		0.0	0.1		0.1	
		4.5	I _O =6.0 mA		0.17	0.26		0.33	
		6.0	I _O =7.8 mA		0.18	0.26		0.33	
I _I	Input Leakage Current	6.0	V _I = V _{CC} or GND			±0.1		±1	μA
I _{oz}	High Impedance Output Leakage Current	6.0	V _I = V _{IH} or V _{IL} V _O = V _{CC} or GND			±0.5		±5	μA
I _{CC}	Quiescent Supply Current	6.0	V _I = V _{CC} or GND			4		40	μA

Table 7. AC electrical characteristics ($C_L = 50\text{pF}$, Input $t_r = t_f = 6\text{ns}$)

Symbol	Parameter	Test Condition			Value					Unit	
		V_{CC} (V)	C_L (pF)		$T_A = 25^\circ\text{C}$			-40 to 85°C			
					Min	Typ	Max	Min	Max		
$t_{TLH} t_{THL}$	Output Transition Time	2.0	50			25	60		75	ns	
		4.5			7	12		15			
		6.0			6	10		13			
$t_{PLH} t_{PHL}$	Propagation Delay Time(LE,D – Q)	2.0	50			42	125		155	ns	
		4.5			14	25		31			
		6.0			12	21		26			
		2.0	150			57	175		220	ns	
		4.5			19	35		44			
		6.0			16	30		37			
$t_{PZL} t_{PZH}$	High Impedance Output Enable Time	2.0	50	$R_L = 1\text{K}\Omega$			39	125		155	ns
		4.5				13	25		31		
		6.0				11	21		26		
		2.0	150	$R_L = 1\text{K}\Omega$			54	175		220	ns
		4.5				18	35		44		
		6.0				15	30		37		
$t_{PLZ} t_{PHZ}$	High Impedance Output Disable Time	2.0	50	$R_L = 1\text{K}\Omega$			30	125		155	ns
		4.5				14	25		31		
		6.0				13	21		26		
$t_{W(H)}$	Minimum Pulse Width(LE)	2.0	50			15	75		95	ns	
		4.5			6	15		19			
		6.0			6	13		16			
t_s	Minimum Set-up Time	2.0	50			16	50		65	ns	
		4.5			4	10		13			
		6.0			3	9		11			
t_h	Minimum Hold Time	2.0	50				5		5	ns	
		4.5				5		5			
		6.0				5		5			

Table 8. Capacitive characteristics

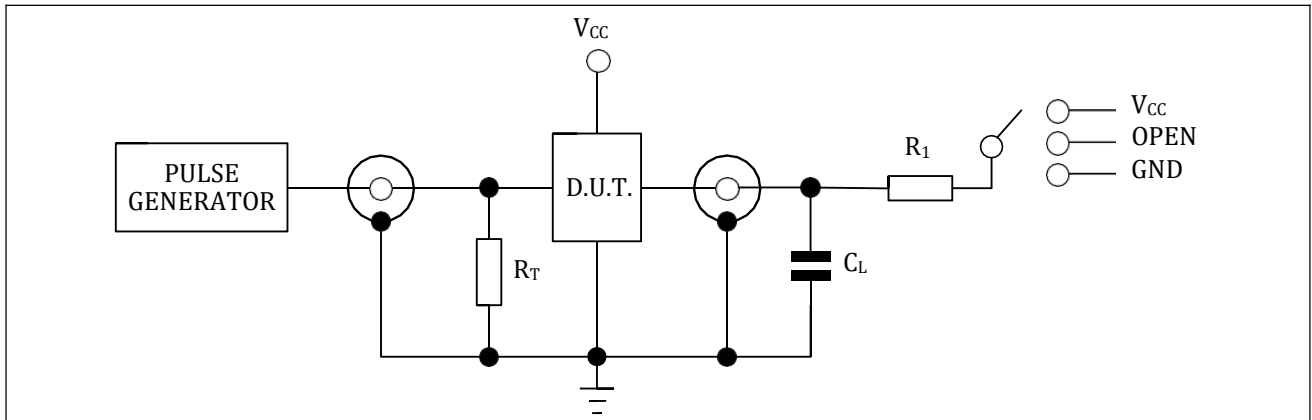
Symbol	Parameter	Test Condition			Value					Unit
		V_{CC} (V)			$T_A = 25^\circ\text{C}$			-40 to 85°C		
					Min	Typ	Max	Min	Max	
C_{IN}	Input Capacitance	5.0				5	10		10	pF
C_{OUT}	Output Capacitance	5.0				10				pF
C_{PD}	Power Dissipation Capacitance ⁽¹⁾	5.0				38				pF

1. C_{PD} is defined as the value of the IC's internal equivalent capacitance which is calculated from the operating current consumption without load. (Refer to test circuit). Average operating current can be obtained by the following equation:
 $I_{CC(opr)} = C_{PD} \times V_{CC} \times f_{IN} + I_{CC}/8$ (per Flip Flop) and the C_{PD} when n pcs of Flip Flop operate, can be gained by the following equation: $C_{PD(TOTAL)} = 22 + 16 \times n$ (pF)



4 Test circuit

Figure 4. Test circuit



TEST	SWITCH
t_{PLH} , t_{PHL}	OPEN
t_{PZL} , t_{PLZ}	Vcc
t_{PZH} , t_{PHZ}	GND

R_T = Z_{OUT} of pulse generator (typically 50Ω)

R_1 = 1KΩ or equivalent

C_L = 50pF/150pF or equivalent (includes jig and probe capacitance)

Figure 5. Waveform 1: LE to Qn propagation delays, LE minimum pulse width, Dn to LE setup and hold time (f=1MHz; 50% duty cycle)

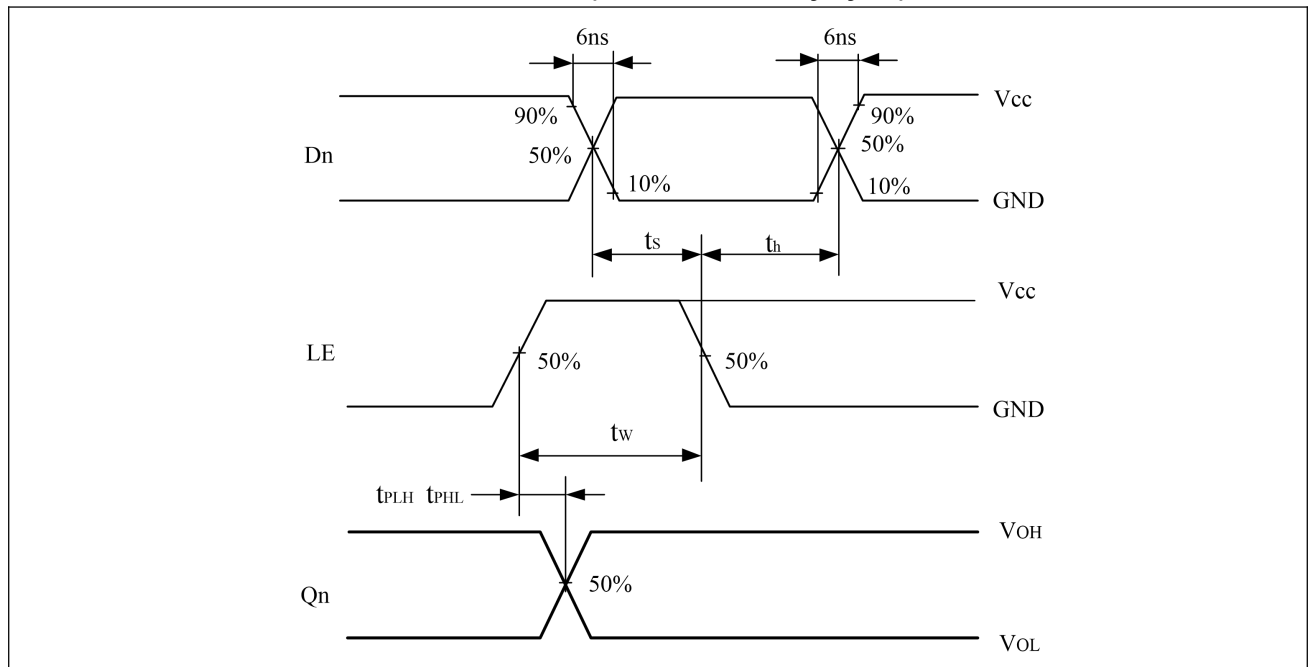
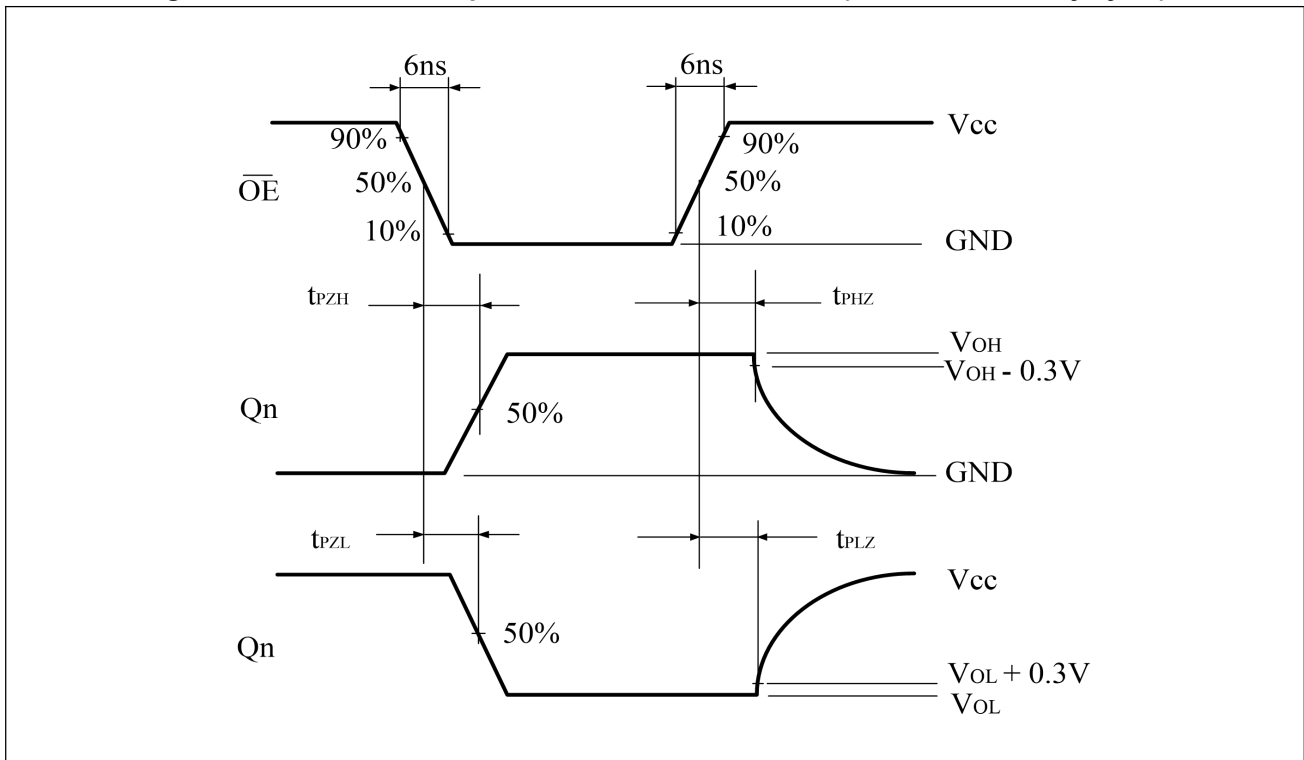
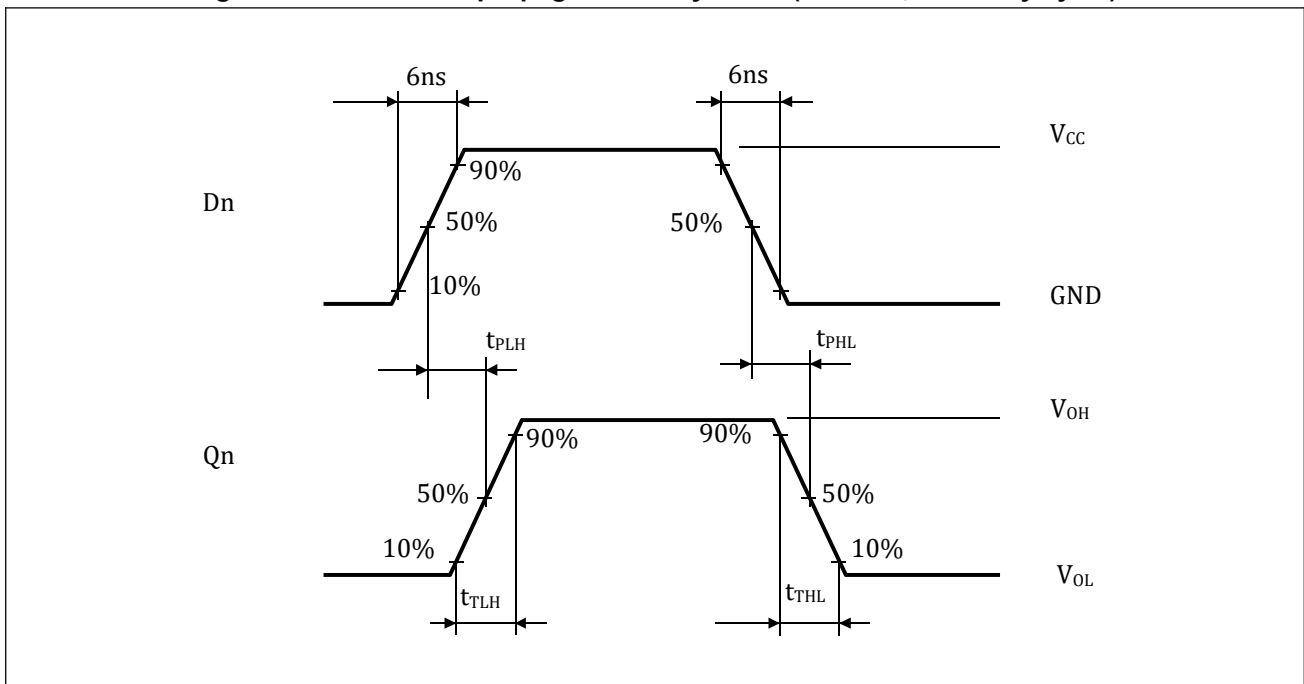
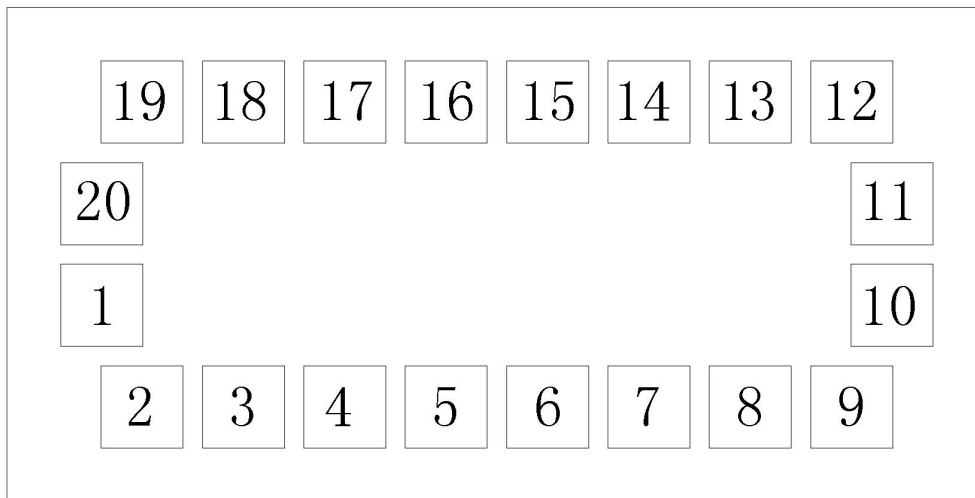


Figure 6. Waveform 2: output enable and disable times ($f = 1\text{MHz}$; 50% duty cycle)Figure 7. Waveform 3: propagation delay times ($f = 1\text{MHz}$; 50% duty cycle)

5 Die Information

Die Type	RD74HC373	Wafer Size	8 Inch
Die Size (μm)	X/Y: 657/331	Bond Area (μm)	X/Y: 55/55
Scribeline (μm)	60	Chip Thickness	
Metal	Front	Al+0.5%Cu	
	Back	Si	
	Top Metal Thickness	9000Å	

(657, 331)



(0, 0)

Pin No.	Pin Name	Coordinate		Pin No.	Pin Name	Coordinate	
		X	Y			X	Y
1	$\overline{\text{OE}}$	63.5	131.5	11	LE	593.5	199.5
2	Q0	90.5	63.5	12	Q4	566.5	267.5
3	D0	158.5	63.5	13	D4	498.5	267.5
4	D1	226.5	63.5	14	D5	430.5	267.5
5	Q1	294.5	63.5	15	Q5	362.5	267.5
6	Q2	362.5	63.5	16	Q6	294.5	267.5
7	D2	430.5	63.5	17	D6	226.5	267.5
8	D3	498.5	63.5	18	D7	158.5	267.5
9	Q3	566.5	63.5	19	Q7	90.5	267.5
10	GND	593.5	131.5	20	V _{CC}	63.5	199.5

6 Ordering information

Table 9. Device summary

Order code	Package	Packing
RD74HC373BDI	DIP20	Tape and reel
RD74HC373BSO	SOP20	
RD74HC373BTS	TSSOP20	
RD74HC373B		Wafer

7 Revision history

Table 10. Document revision history ⁽¹⁾

Date	Revision	Changes
18-Jan-2022	1	Initial release
12-Dec-2023	2	Added : Die information Revised document presentation, minor textual updates

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